

GSDS103XWS Series

Schottky Barrier Diodes

Product Description

Schottky Barrier Diodes 200mW / 20V~40V

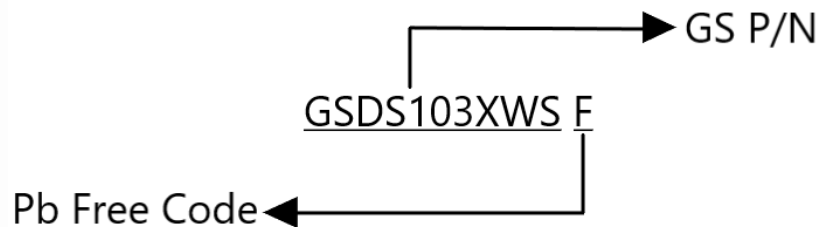
Features

- Low Forward Voltage Drop
- Flat Lead SOD-323 Small Outline Plastic Package
- Surface Device Type Mounting
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicates Cathode
- Weight: approx. 0.004g

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit diagram
GSDS103AWSF	SOD-323	JV	
GSDS103BWSF	SOD-323	JW	
GSDS103CWSF	SOD-323	JX	

Ordering Information



Part Number	Package	Quantity
GSDS103AWSF	SOD-323	3000 PCS
GSDS103BWSF	SOD-323	
GSDS103CWSF	SOD-323	

Absolute Maximum Rating (TA=25°C Unless otherwise noted)

Symbol	Parameter	Value	Units	
P _D	Power Dissipation	200	mW	
T _{STG}	Storage Temperature Range	-65 to +125	°C	
T _J	Operating Junction Temperature	+125	°C	
V _{RM}	Repetitive Peak Reverse Voltage	GSDS103AWS GSDS103BWS GSDS103CWS	40 30 20	V
I _{F(AV)}	Average Forward Rectified Current	200	mA	
I _{FSM}	Peak Forward Surge Current (10uS square wave)	2	A	

These ratings are limiting values above which the serviceability of the diode may be impaired.

Electrical Characteristics (TA=25°C Unless otherwise noted)

Symbol	Parameter	Test Condition	Limits	Unit	
I _R	Reverse Leakage Current	GSDS103AWS GSDS103BWS GSDS103CWS	V _R =30V V _R =20V V _R =10V	5	μA
V _F	Forward Voltage	I _F =20mA I _F =200mA	0.37 0.60	Volts	
C _t	Junction Capacitance	f=1MHZ, V _R =0V	50	pF	

Typical Characteristics

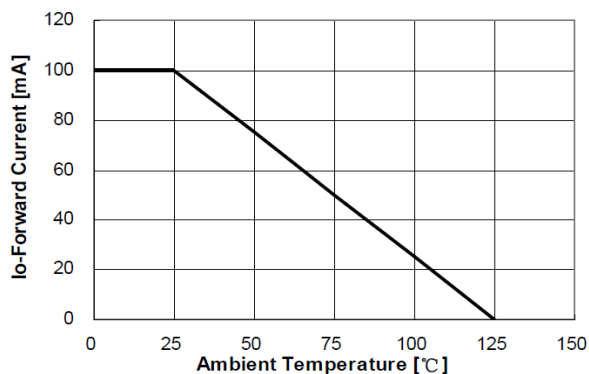


Figure 1. Forward Current Derating Curve

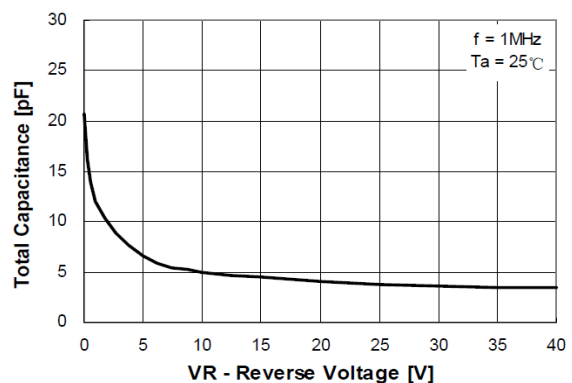


Figure 2. Total Capacitance

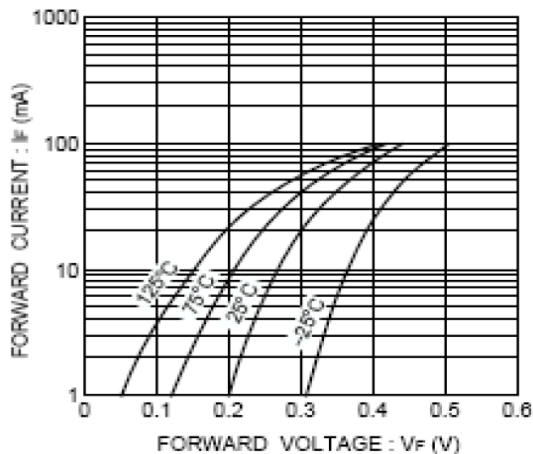


Figure 3. Forward Characteristics

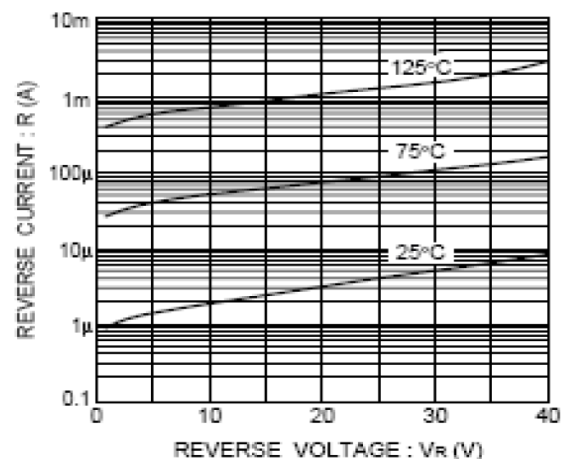
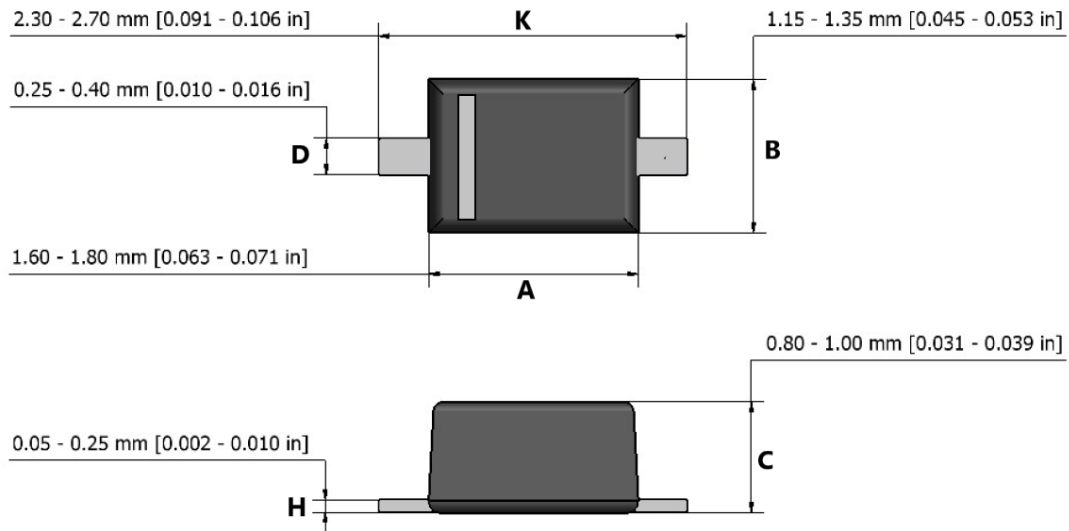


Figure 4. Reverse Characteristics

Package Dimension

SOD-323



NOTES:

1. The above package outline is similar to JEITA SC-90.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.





Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.6	1.8	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.8	1	0.031	0.039
D	0.25	0.4	0.01	0.016
H	0.05	0.25	0.002	0.01
K	2.3	2.7	0.091	0.106



Pin 1.CATHODE
Pin 2.ANODE

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